

To: Distribution List

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## ***NEW PRODUCT ANNOUNCEMENT***

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### **AMCOM' s 3.2 W ( $P_{1dB}$ : 35 dBm) GaAs FET–DC to 6 GHZ**

AMCOM recently released **AM 100MX-CU** GaAs FET as part of a series of GaAs MESFET power products . This device has a total gate width of 10.0mm and is offered in a specially designed ceramic package with straight leads and flange in a drop-in mounting style. The flange at the bottom of the package serves simultaneously as DC ground, RF ground and thermal path. This device offers RF power levels in-between AMCOM' s previously released **AM 072MX-CU** and **AM 150MX-CU** GaAs FET products with RF Power up to 4W. As part of this product series AMCOM also offers **AM200MX-CU** and **AM300MX-CU** devices with RF Power up to 10W.

Typical Performance for AM 100MX-CU device at 4.0 GHz ( $T_A=25$  degrees C) when  $V_{DS}= 7V$  and  $I_{ds}=0.5I_{dss}$  is:  $P_{1dB}=35dBm$ ; Eff @  $P_{1dB}= 37\%$ ; Gain ( small signal) 10 dB,  $IP_3=48dBm$ . It is well suited for wireless communications applications including WLAN,MMDS/MDS, PCS base stations, Repeaters & Hyperlan.

Data sheets are available at AMCOM' s web site [www.amcomusa.com](http://www.amcomusa.com) . Please contact the Clarksburg, MD facility for availability and pricing.